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## Is Now



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# J309, J310

**Preferred Device** 

# **JFET VHF/UHF Amplifiers**

## **N-Channel** — Depletion

## **Features**

• Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

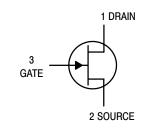
Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	Vdc
Gate - Source Voltage	V <sub>GS</sub>	25	Vdc
Forward Gate Current	I <sub>GF</sub>	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above = 25°C	P <sub>D</sub>	350 2.8	mW mW/°C
Junction Temperature Range	TJ	-65 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



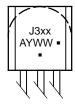
## ON Semiconductor®

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## **MARKING DIAGRAM**



J3xx = Device Code

xx = 09 or 10

= Assembly Location

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

J309/D

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## J309, J310

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

·	•	•	•	
V <sub>(BR)GSS</sub>	-25	_	_	Vdc
I <sub>GSS</sub>		_ _	-1.0 -1.0	nAdc μAdc
	-1.0 -2.0	- -	-4.0 -6.5	Vdc
	12 24	_ _	30 60	mAdc
V <sub>GS(f)</sub>	-	_	1.0	Vdc
	_ _	0.7 0.5	_ _	mmhos
Re(y <sub>os</sub> )	-	0.25	_	mmhos
G <sub>pg</sub>	-	16	_	dB
Re(y <sub>fs</sub> )	_	12	_	mmhos
Re(y <sub>ig</sub> )	-	12	_	mmhos
	10000 8000		20000 18000	μmhos
gos	-	_	250	μmhos
	- -	13000 12000	_ _	μmhos
	_ _	100 150	_ _	μmhos
C <sub>gd</sub>	-	1.8	2.5	pF
C <sub>gs</sub>	-	4.3	5.0	pF
•		•	•	•
ē <sub>n</sub>	_	10	_	nV/√ <del>Hz</del>
	V <sub>GS(off)</sub> V <sub>GS(off)</sub> V <sub>GS(off)</sub> V <sub>GS(f)</sub> V <sub>GS(f)</sub> Re(y <sub>is</sub> )  Re(y <sub>is</sub> )  Re(y <sub>ig</sub> )  G <sub>pg</sub> Re(y <sub>ig</sub> )  G <sub>pg</sub> G <sub>o</sub>	C		

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  3.0%.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
J309	TO-92	
J309G	TO-92 (Pb-Free)	1000 Units / Bulk
J310	TO-92	
J310G	TO-92 (Pb-Free)	1000 Units / Bulk
J310RLRP	TO-92	
J310RLRPG	TO-92 (Pb-Free)	2000 Units / Tape & Ammo Box
J310ZL1	TO-92	
J310ZL1G	TO-92 (Pb-Free)	2000 Units / Tape & Ammo Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

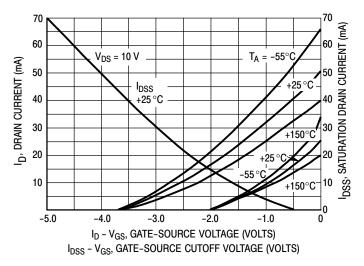


Figure 1. Drain Current and Transfer Characteristics versus Gate-Source Voltage

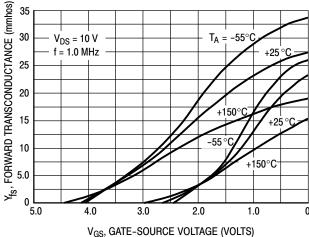


Figure 2. Forward Transconductance versus Gate-Source Voltage

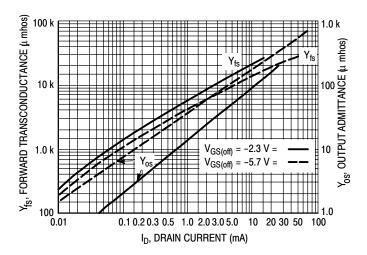


Figure 3. Common–Source Output
Admittance and Forward Transconductance
versus Drain Current

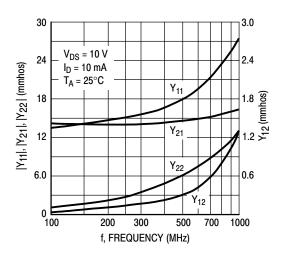


Figure 5. Common-Gate Y Parameter Magnitude versus Frequency

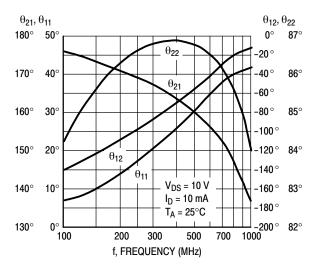


Figure 7. Common–Gate Y Parameter Phase–Angle versus Frequency

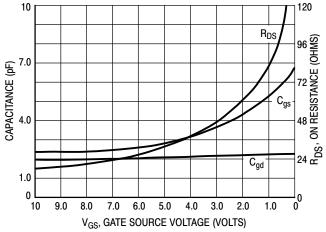


Figure 4. On Resistance and Junction Capacitance versus Gate-Source Voltage

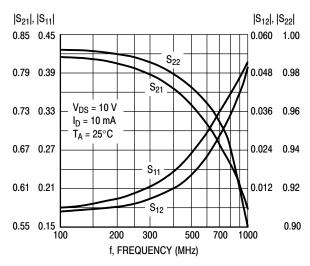


Figure 6. Common-Gate S Parameter Magnitude versus Frequency

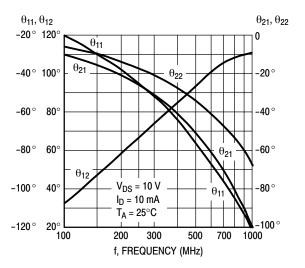
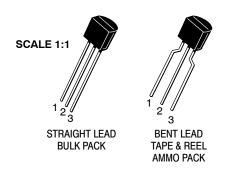
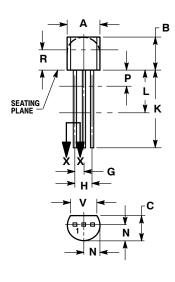


Figure 8. S Parameter Phase–Angle versus Frequency



**TO-92 (TO-226)** CASE 29-11 **ISSUE AM** 

**DATE 09 MAR 2007** 

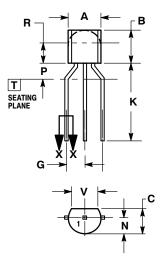


STRAIGHT LEAD **BULK PACK** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPE & REEL AMMO PACK



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

## **STYLES ON PAGE 2**

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# **TO-92 (TO-226)** CASE 29-11

# ISSUE AM

## DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE		
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE ANODE
2. 3.	ANODE CATHODE & ANODE CATHODE	2. 3.	GATE MAIN TERMINAL 2	2. 3.	GATE CATHODE 2	2. 3.	COLLECTOR BASE	2. 3.	CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
PIN 1. 2.	EMITTER	PIN 1.	SOURCE GATE	PIN 1.	GATE SOURCE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
2.	V <sub>CC</sub> GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	DRAIN
2.	GATE	PIN 1. 2.	BASE COLLECTOR	PIN 1.	RETURN INPUT	PIN 1. 2.	INPUT		GATE

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#### PAGE 3 OF 3

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AM	ADDED BENT-LEAD TAPE & REEL VERSION. REQ. BY J. SUPINA.	09 MAR 2007

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